

PMBTA42DS

NPN/NPN high-voltage double transistors

Rev. 02 — 27 August 2009

Product data sheet

1. Product profile

1.1 General description

NPN/NPN high-voltage double transistors in a small SOT457 (SC-74) Surface Mounted Device (SMD) plastic package.

1.2 Features

- High breakdown voltage
- Two electrically isolated transistors
- Small SMD plastic package

1.3 Applications

- Automotive:
 - ◆ High- and low-side switches
 - ◆ Voltage regulators
- Communication: Telecom line interface
- Consumer: CRT TV
- Computing: Monitors

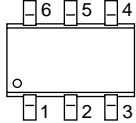
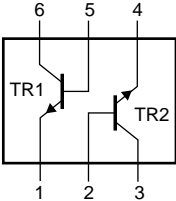
1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
V_{CEO}	collector-emitter voltage	open base	-	-	300	V
I_C	collector current		-	-	100	mA
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	200	mA

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	emitter TR1		
2	base TR2		
3	collector TR2		
4	emitter TR2		
5	base TR1		
6	collector TR1		

006aaa677

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMBTA42DS	SC-74	plastic surface mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 4. Marking codes

Type number	Marking code
PMBTA42DS	P4

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
Per transistor						
V_{CBO}	collector-base voltage	open emitter	-	300	V	
V_{CEO}	collector-emitter voltage	open base	-	300	V	
V_{EBO}	emitter-base voltage	open collector	-	6	V	
I_C	collector current		-	100	mA	
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	200	mA	
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	-	100	mA	
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	290	mW
			[2]	-	370	mW
			[3]	-	450	mW

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
Per device						
P_{tot}	total power dissipation	$T_{\text{amb}} \leq 25\text{ °C}$	[1]	-	420	mW
			[2]	-	560	mW
			[3]	-	700	mW
T_j	junction temperature		-	150	°C	
T_{amb}	ambient temperature		-65	+150	°C	
T_{stg}	storage temperature		-65	+150	°C	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
$R_{\text{th}(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	431	K/W
			[2]	-	338	K/W
			[3]	-	278	K/W
$R_{\text{th}(j-sp)}$	thermal resistance from junction to solder point		-	-	105	K/W
Per device						
$R_{\text{th}(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	298	K/W
			[2]	-	223	K/W
			[3]	-	179	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

7. Characteristics

Table 7. Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
I_{CBO}	collector-base cut-off current	$V_{CB} = 200\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 6\text{ V}; I_C = 0\text{ A}$	-	-	100	nA
h_{FE}	DC current gain	$V_{CE} = 10\text{ V}; I_C = 1\text{ mA}$	25	-	-	
		$V_{CE} = 10\text{ V}; I_C = 10\text{ mA}$	40	-	-	
		$V_{CE} = 10\text{ V}; I_C = 30\text{ mA}$	40	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 20\text{ mA}; I_B = 2\text{ mA}$	-	-	500	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 20\text{ mA}; I_B = 2\text{ mA}$	-	-	900	mV
C_{re}	feedback capacitance	$V_{CB} = 20\text{ V}; I_C = i_c = 0\text{ A}; f = 1\text{ MHz}$	-	-	3	pF
f_T	transition frequency	$V_{CE} = 20\text{ V}; I_C = 10\text{ mA}; f = 100\text{ MHz}$	50	-	-	MHz

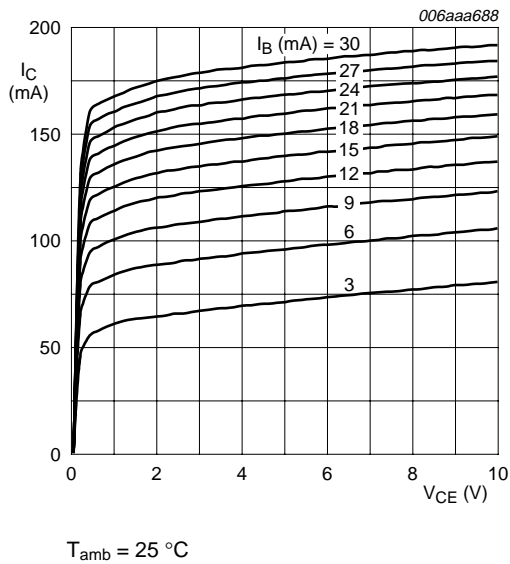


Fig 1. Collector current as a function of collector-emitter voltage; typical values

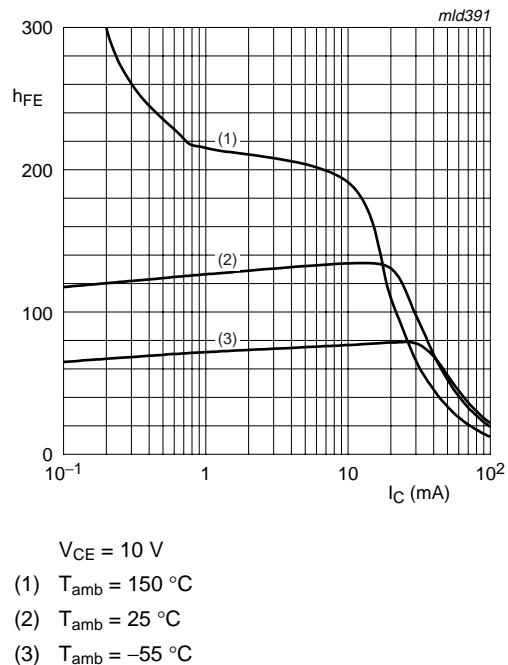
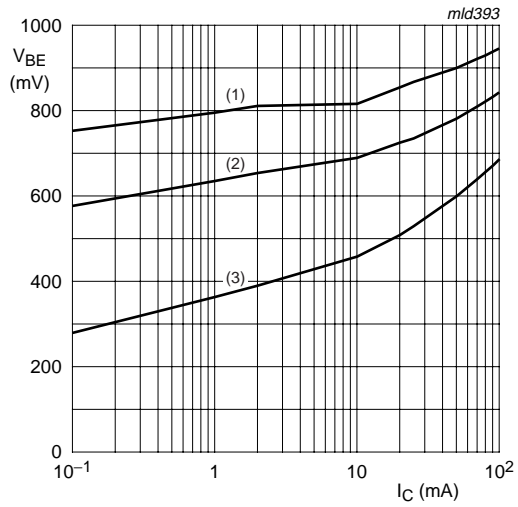
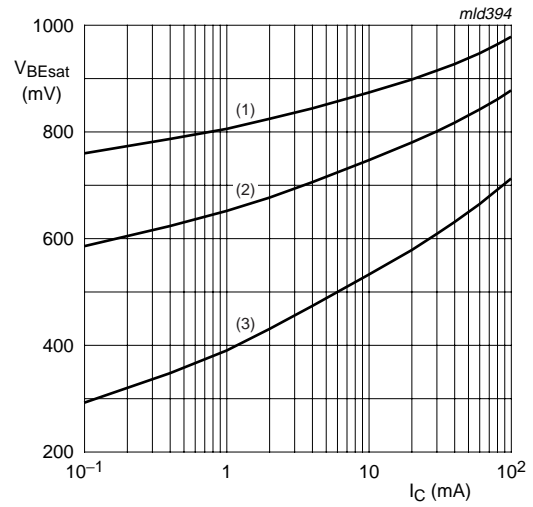


Fig 2. DC current gain as a function of collector current; typical values



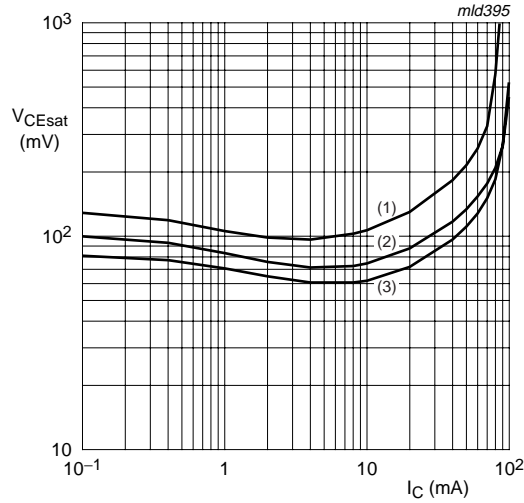
$V_{CE} = 10\text{ V}$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig 3. Base-emitter voltage as a function of collector current; typical values



$I_C/I_B = 10$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

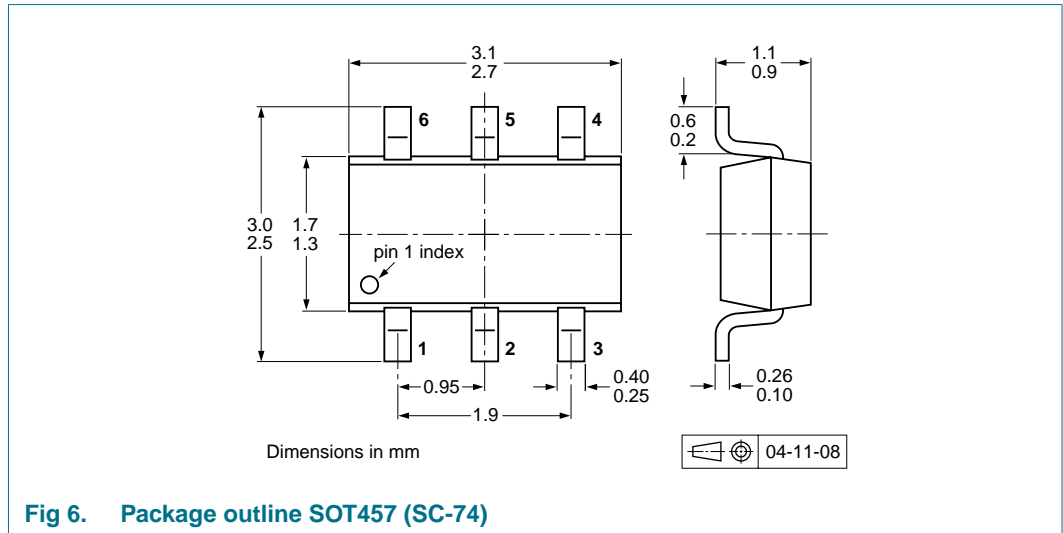
Fig 4. Base-emitter saturation voltage as a function of collector current, typical values



$I_C/I_B = 10$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values

8. Package outline



9. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

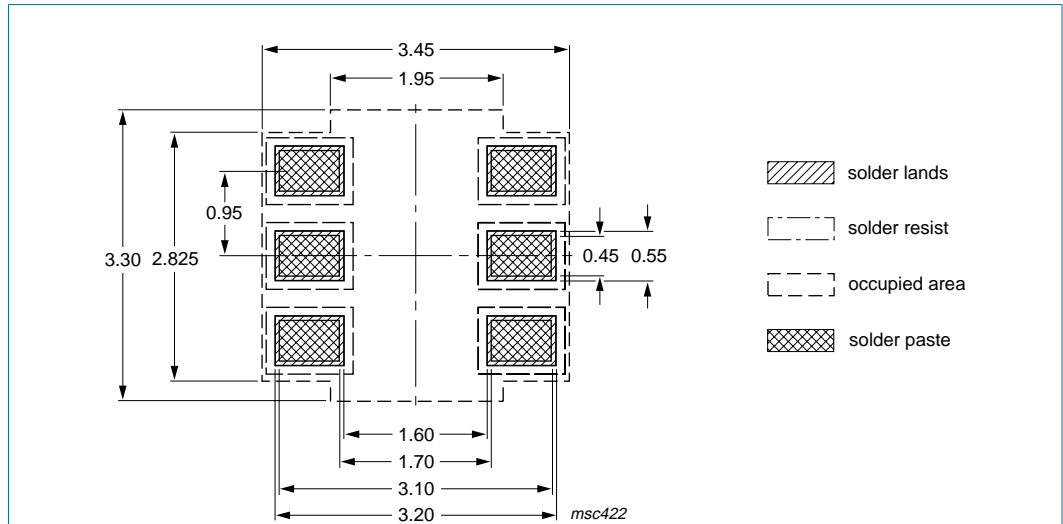
Type number	Package	Description	Packing quantity	
			3000	10000
PMBTA42DS	SOT457	4 mm pitch, 8 mm tape and reel; T1 ^[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2 ^[3]	-125	-165

[1] For further information and the availability of packing methods, see [Section 13](#).

[2] T1: normal taping

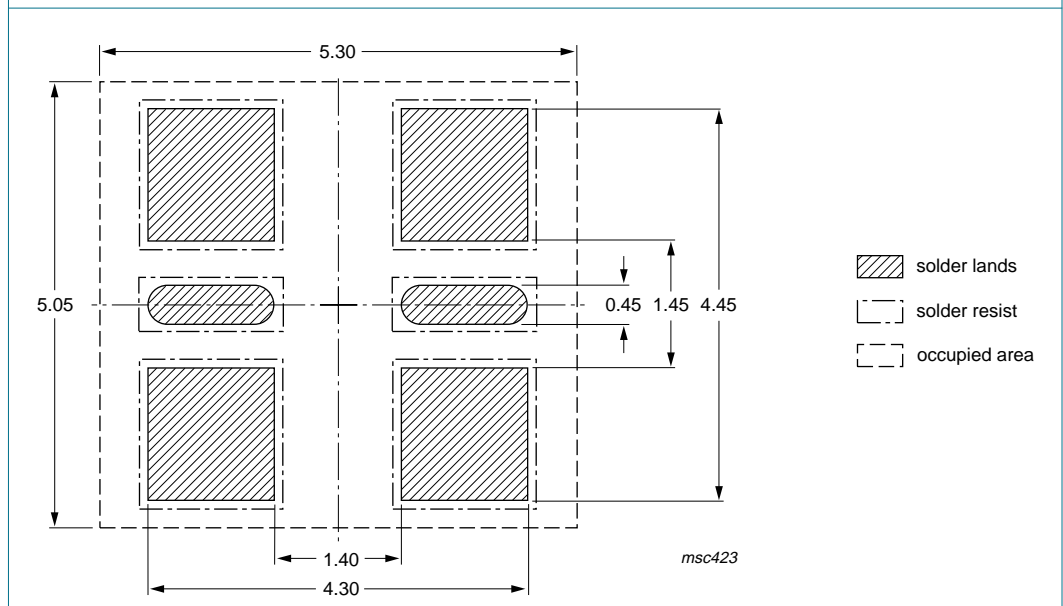
[3] T2: reverse taping

10. Soldering



Dimensions in mm

Fig 7. Reflow soldering footprint SOT457 (SC-74)



Dimensions in mm

Fig 8. Wave soldering footprint SOT457 (SC-74)

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBTA42DS_2	20090827	Product data sheet	-	PMBTA42DS_1
Modifications:		<ul style="list-style-type: none">This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.Figure 8 "Wave soldering footprint SOT457 (SC-74)":updated		
PMBTA42DS_1	20060106	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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14. Contents

1 Product profile 1

1.1 General description 1

1.2 Features 1

1.3 Applications 1

1.4 Quick reference data 1

2 Pinning information 2

3 Ordering information 2

4 Marking 2

5 Limiting values 2

6 Thermal characteristics 3

7 Characteristics 4

8 Package outline 6

9 Packing information 6

10 Soldering 7

11 Revision history 8

12 Legal information 9

12.1 Data sheet status 9

12.2 Definitions 9

12.3 Disclaimers 9

12.4 Trademarks 9

13 Contact information 9

14 Contents 10

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